

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2761

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

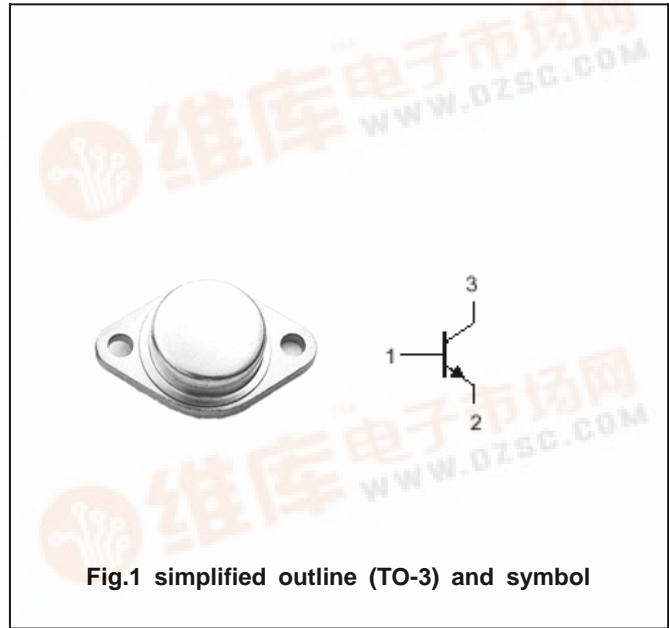


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	450	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		30	A
I <sub>B</sub>	Base current		6	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	200	W
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	400			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1m A ; I <sub>E</sub> =0	450			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1m A ; I <sub>C</sub> =0	7			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =20A; I <sub>B</sub> =4A			1.5	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =20A; I <sub>B</sub> =4A			1.7	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =450V I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =15A ; V <sub>CE</sub> =2V	8			

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PACKAGE OUTLINE

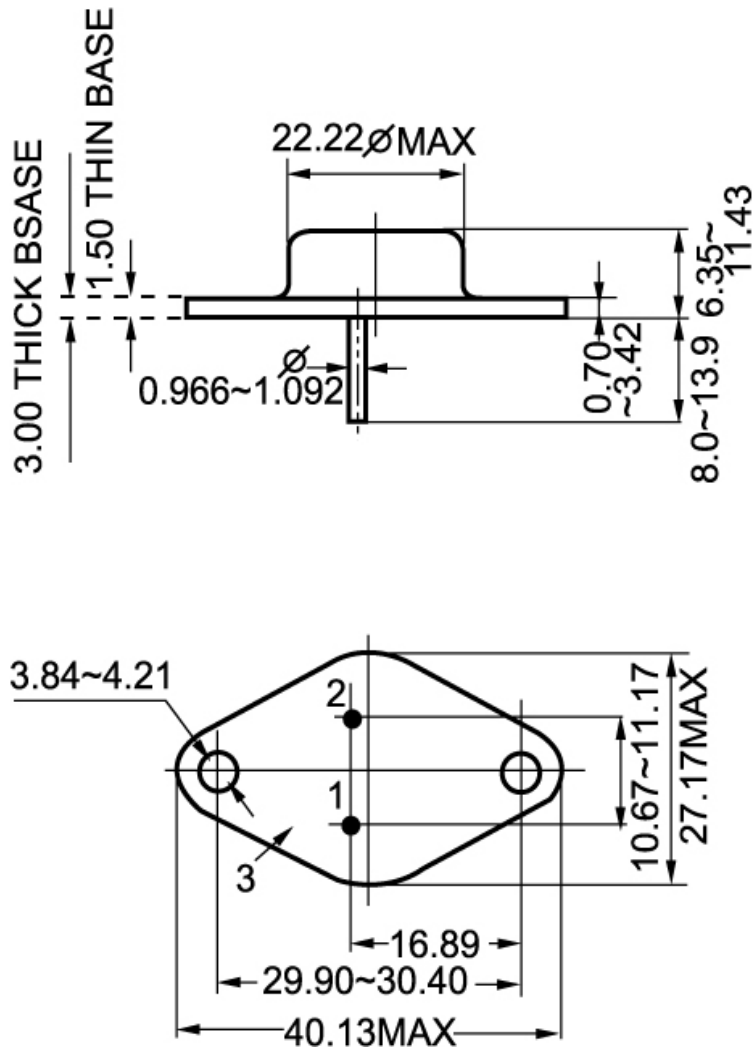


Fig.2 Outline dimensions